

Product features

High precision machining technology

Low temperature drift, high power.

Ceramic substrate, 50 Ω coplanar waveguide

Gold wire bonding

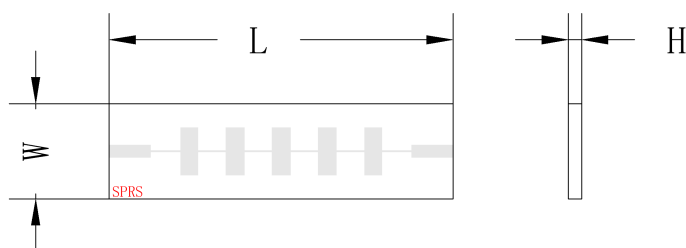
Tech specifications

Items	Parameters	Units
Center Frequency	6.7	GHz
Bandwidth	DC-13.4	GHz
Passband IL	2.0	dB
Ripple	2.0	dB
VSWR	1.5:1	
Group delay ripple	0.4	ns
Rejection	50@17.5-23.0GHz	dBc
Rejection	45@23.0-33.0GHz	dBc

Other requirement (Design assurance)

power	0.5W CW
Operation Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L:4.0, W:2.0, h:0.26

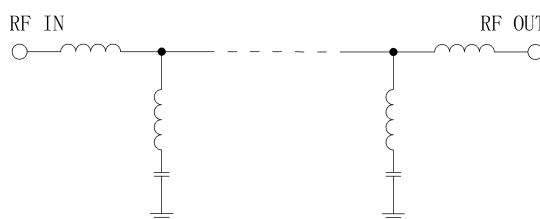
Outline drawing: Port centered



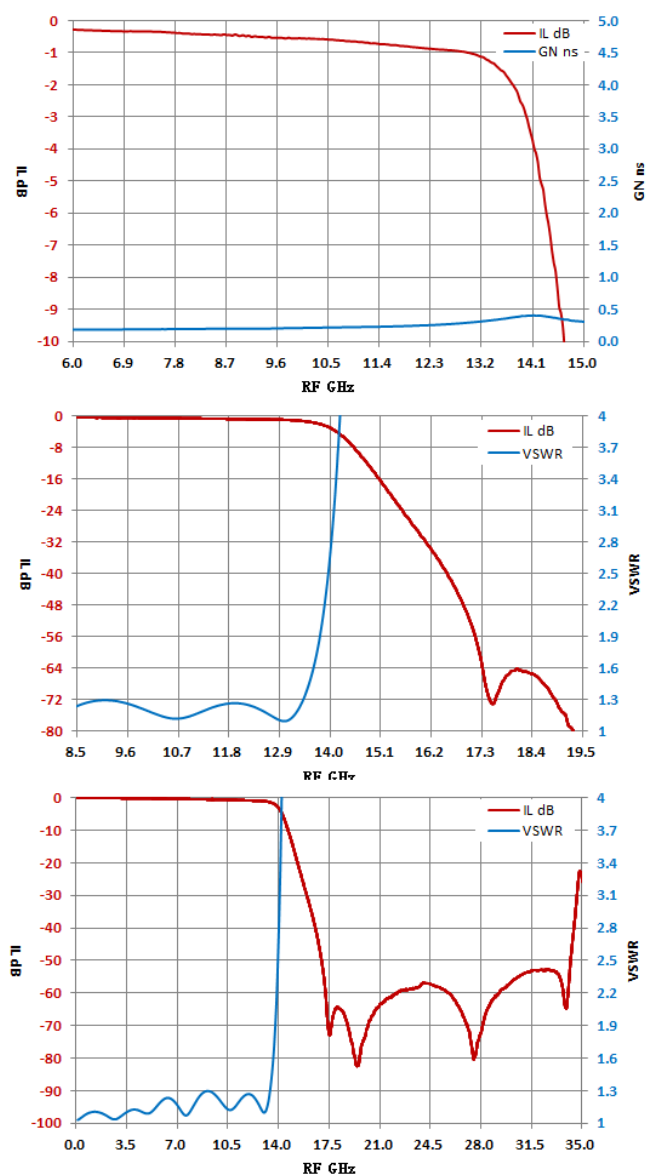
Reference picture



Schematic diagram

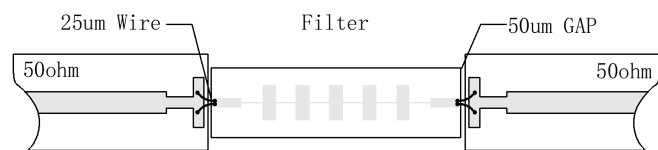


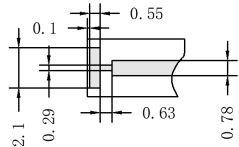
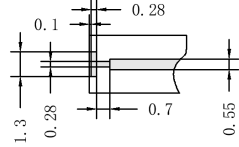
Typical test curve



Note: The specifications and performance data contained in this data sheet are based on tests established by CMW.

Suggested PCB Layout



PCB Rogers5880, h:0.254mm	PCB Rogers4350B, h:0.254mm
	

Note

- 1: The chip is recommended to be used in separate chambers, with one side 0.1mm away from the side wall and the surface 1.74mm away from the top cover. The ports are interchangeable;
- 2: Suggest using conductive adhesive for bonding;
- 3: 芯片应安装在可伐(推荐) 或铜等与陶瓷热膨胀系数(6.7ppm /C)相近的材料, 载体厚度 $\geq 0.2\text{mm}$;
- 4: Suggest using a T-shaped structure for microstrip bonding.